

Title (en)

Film-forming surface reforming method and semiconductor device manufacturing method

Title (de)

Oberflächenvorbehandlungsmethode und Halbleiterherstellungsmethode

Title (fr)

Traitement de la surface pour le dépôt d'une couche et méthode de fabrication d'un dispositif semiconducteur

Publication

**EP 1139399 A3 20030205 (EN)**

Application

**EP 01106454 A 20010323**

Priority

- JP 2000098262 A 20000331
- JP 2001001759 A 20010109

Abstract (en)

[origin: EP1139399A2] There is provided a film-forming surface reforming method that comprises the steps of bringing a gas or an aqueous solution containing ammonia, hydrazine, amine, amino compound or their derivative into contact with a film-forming surface (12a) before an insulating film (15) is formed on the film-forming surface (12a) of a substrate (102), and bringing a gas or an aqueous solution containing hydrogen peroxide, ozone, oxygen, nitric acid, sulfuric acid or their derivative into contact with the film-forming surface (12a). <IMAGE>

IPC 1-7

**H01L 21/306**; H01L 21/316; C23C 16/02

IPC 8 full level

**H01L 21/20** (2006.01); **C23C 16/02** (2006.01); **C23C 16/34** (2006.01); **C23C 16/40** (2006.01); **H01L 21/302** (2006.01); **H01L 21/316** (2006.01)

CPC (source: EP KR US)

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Citation (search report)

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